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Understanding Embedded - Microprocessors

Embedded microprocessors are specialized computing chips designed to perform specific tasks within an embedded system. Unlike general-purpose microprocessors found in personal computers, embedded microprocessors are tailored for dedicated functions within larger systems, offering optimized performance, efficiency, and reliability. These microprocessors are integral to the operation of countless electronic devices, providing the computational power necessary for controlling processes, handling data, and managing communications.

Applications of Embedded - Microprocessors

Embedded microprocessors are utilized across a broad spectrum of applications, making them indispensable in

Details	
Product Status	Active
Core Processor	PowerPC e300c3
Number of Cores/Bus Width	1 Core, 32-Bit
Speed	266MHz
Co-Processors/DSP	Communications; QUICC Engine
RAM Controllers	DDR2
Graphics Acceleration	No
Display & Interface Controllers	-
Ethernet	10/100Mbps (3)
SATA	-
USB	USB 2.0 (1)
Voltage - I/O	1.8V, 3.3V
Operating Temperature	-40°C ~ 105°C (TA)
Security Features	-
Package / Case	369-LFBGA
Supplier Device Package	369-PBGA (19x19)
Purchase URL	https://www.e-xfl.com/pro/item?MUrl=&PartUrl=mpc8306scvmaddca

In summary, the MPC8306S provides users with a highly integrated, fully programmable communications processor. This helps to ensure that a low-cost system solution can be quickly developed and offers flexibility to accommodate new standards and evolving system requirements.

1.1 Features

The major features of the device are as follows:

- e300c3 Power Architecture processor core
  - Enhanced version of the MPC603e core
  - High-performance, superscalar processor core with a four-stage pipeline and low interrupt latency times
  - Floating-point, dual integer units, load/store, system register, and branch processing units
  - 16-Kbyte instruction cache and 16-Kbyte data cache with lockable capabilities
  - Dynamic power management
  - Enhanced hardware program debug features
  - Software-compatible with Freescale processor families implementing Power Architecture technology
  - Separate PLL that is clocked by the system bus clock
  - Performance monitor
- QUICC Engine block
  - 32-bit RISC controller for flexible support of the communications peripherals with the following features:
    - One clock per instruction
    - Separate PLL for operating frequency that is independent of system's bus and e300 core frequency for power and performance optimization
    - 32-bit instruction object code
    - Executes code from internal IRAM
    - 32-bit arithmetic logic unit (ALU) data path
    - Modular architecture allowing for easy functional enhancements
    - Slave bus for CPU access of registers and multiuser RAM space
    - 48 Kbytes of instruction RAM
    - 16 Kbytes of multiuser data RAM
    - Serial DMA channel for receive and transmit on all serial channels
  - Five unified communication controllers (UCCs) supporting the following protocols and interfaces:
    - 10/100 Mbps Ethernet/IEEE Std. 802.3® through MII and RMII interfaces.
    - HDLC/Transparent (bit rate up to QUICC Engine operating frequency / 8)
    - HDLC Bus (bit rate up to 10 Mbps)
    - Asynchronous HDLC (bit rate up to 2 Mbps)

  - The power management controller detects that the system is not idle and there are outstanding transactions on the internal bus or an external interrupt.
- Parallel I/O
  - General-purpose I/O (GPIO)
    - 56 parallel I/O pins multiplexed on various chip interfaces
    - Interrupt capability
- System timers
  - Periodic interrupt timer
  - Software watchdog timer
  - Eight general-purpose timers
- Real time clock (RTC) module
  - Maintains a one-second count, unique over a period of thousands of years
  - Two possible clock sources:
    - External RTC clock (RTC_PIT_CLK)
    - CSB bus clock
- IEEE Std. 1149.1™ compliant JTAG boundary scan

2 Electrical Characteristics

This section provides the AC and DC electrical specifications and thermal characteristics for the MPC8306S. The MPC8306S is currently targeted to these specifications. Some of these specifications are independent of the I/O cell, but are included for a more complete reference. These are not purely I/O buffer design specifications.

2.1 Overall DC Electrical Characteristics

This section covers the ratings, conditions, and other characteristics.

2.1.1 Absolute Maximum Ratings

The following table provides the absolute maximum ratings.

Table 1. Absolute Maximum Ratings[1]

Characteristic	Symbol	Max Value	Unit	Notes
Core supply voltage	V_{DD}	–0.3 to 1.26	V	—
PLL supply voltage	AV_{DD1} AV_{DD2} AV_{DD3}	–0.3 to 1.26	V	—
DDR2 DRAM I/O voltage	GV_{DD}	–0.3 to 1.98	V	—
Local bus, DUART, system control and power management, I^2C, SPI, MII, RMII, MII management, USB and JTAG I/O voltage	OV_{DD}	–0.3 to 3.6	V	2

2.1.2 Power Supply Voltage Specification

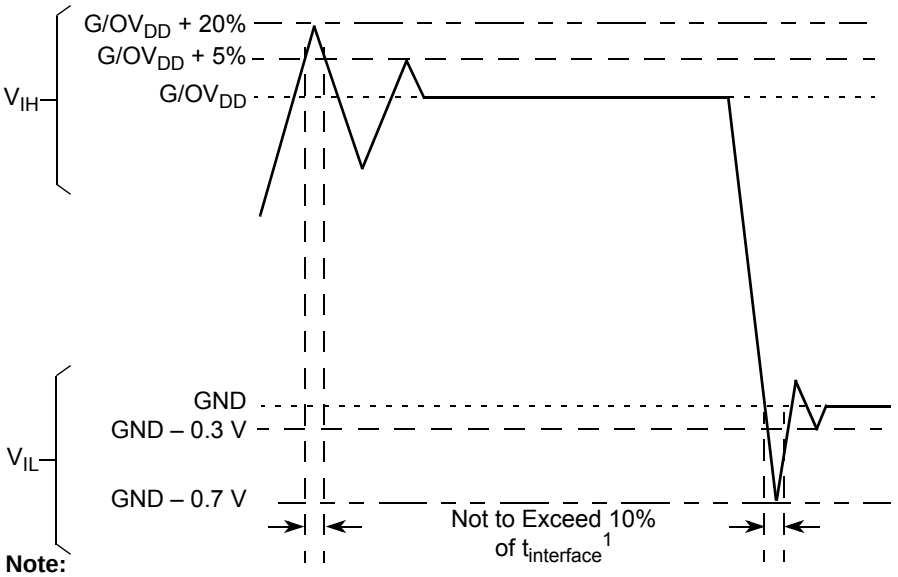
The following table provides the recommended operating conditions for the MPC8306S. Note that these values are the recommended and tested operating conditions. Proper device operation outside of these conditions is not guaranteed.

Table 2. Recommended Operating Conditions

Characteristic	Symbol	Recommended Value	Unit	Note
Core supply voltage	V_{DD}	1.0 V ± 50 mV	V	1
PLL supply voltage	AV_{DD1} AV_{DD2} AV_{DD3}	1.0 V ± 50 mV	V	1
DDR2 DRAM I/O voltage	GV_{DD}	1.8 V ± 100 mV	V	1
Local bus, DUART, system control and power management, I^2C, SPI, MII, RMII, MII management, USB and JTAG I/O voltage	OV_{DD}	3.3 V ± 300 mV	V	1, 3
Junction temperature	T_A/T_J	0 to 105	°C	2

Notes:
1. GV_{DD}, OV_{DD}, AV_{DD}, and V_{DD} must track each other and must vary in the same direction—either in the positive or negative direction.
2. Minimum temperature is specified with T_A(Ambient Temperature); maximum temperature is specified with T_J(Junction Temperature).
3. OVDD here refers to NVDDA, NVDDB, NVDDC, NVDDF, NVDDG, and NVDDH from the ball map.

The following figure shows the undershoot and overshoot voltages at the interfaces of the MPC8306S



Note:
1. $t_{interface}$ refers to the clock period associated with the bus clock interface.

Figure 2. Overshoot/Undershoot Voltage for GV_{DD}/OV_{DD}

The following table provides the PLL lock times.

Table 10. PLL Lock Times

Parameter/Condition	Min	Max	Unit	Note
PLL lock times	—	100	μs	—

5.1 Reset Signals DC Electrical Characteristics

The following table provides the DC electrical characteristics for the MPC8306S reset signals mentioned in Table 9.

Table 11. Reset Signals DC Electrical Characteristics

Characteristic	Symbol	Condition	Min	Max	Unit	Note
Output high voltage	V_{OH}	I_{OH} = –6.0 mA	2.4	—	V	1
Output low voltage	V_{OL}	I_{OL} = 6.0 mA	—	0.5	V	1
Output low voltage	V_{OL}	I_{OL} = 3.2 mA	—	0.4	V	1
Input high voltage	V_{IH}	—	2.0	OV_{DD} + 0.3	V	1
Input low voltage	V_{IL}	—	–0.3	0.8	V	—
Input current	I_{IN}	0 V ≤ V_{IN} ≤ OV_{DD}	—	±5	μA	—

Note:
1. This specification applies when operating from 3.3 V supply.

6 DDR2 SDRAM

This section describes the DC and AC electrical specifications for the DDR2 SDRAM interface of the MPC8306S. Note that DDR2 SDRAM is GV_{DD}(typ) = 1.8 V.

6.1 DDR2 SDRAM DC Electrical Characteristics

The following table provides the recommended operating conditions for the DDR2 SDRAM component(s) of the MPC8306S when GV_{DD}(typ) = 1.8 V.

Table 12. DDR2 SDRAM DC Electrical Characteristics for GV_{DD}(typ) = 1.8 V

Parameter/Condition	Symbol	Min	Max	Unit	Note
I/O supply voltage	GV_{DD}	1.7	1.9	V	1
I/O reference voltage	MVREF	0.49 × GV_{DD}	0.51 × GV_{DD}	V	2
I/O termination voltage	V_{TT}	MVREF – 0.04	MVREF + 0.04	V	3
Input high voltage	V_{IH}	MVREF+ 0.125	GV_{DD} + 0.3	V	—
Input low voltage	V_{IL}	–0.3	MVREF – 0.125	V	—
Output leakage current	I_{OZ}	–9.9	9.9	μA	4

Table 12. DDR2 SDRAM DC Electrical Characteristics for GV_{DD}(typ) = 1.8 V (continued)

Parameter/Condition	Symbol	Min	Max	Unit	Note
Output high current (V_{OUT} = 1.35 V)	I_{OH}	–13.4	—	mA	—
Output low current (V_{OUT} = 0.280 V)	I_{OL}	13.4	—	mA	—

Notes:
1. GV_{DD} is expected to be within 50 mV of the DRAM GV_{DD} at all times.
2. MVREF is expected to be equal to 0.5 × GV_{DD}, and to track GV_{DD} DC variations as measured at the receiver. Peak-to-peak noise on MVREF may not exceed ±2% of the DC value.
3. V_{TT} is not applied directly to the device. It is the supply to which far end signal termination is made and is expected to be equal to MVREF. This rail should track variations in the DC level of MVREF.
4. Output leakage is measured with all outputs disabled, 0 V ≤ V_{OUT} ≤ GV_{DD}.

The following table provides the DDR2 capacitance when GV_{DD}(typ) = 1.8 V.

Table 13. DDR2 SDRAM Capacitance for GV_{DD}(typ) = 1.8 V

Parameter/Condition	Symbol	Min	Max	Unit	Note
Input/output capacitance: DQ, DQS	C_{IO}	6	8	pF	1
Delta input/output capacitance: DQ, DQS	C_{DIO}	—	0.5	pF	1

Note:
1. This parameter is sampled. GV_{DD} = 1.8 V ± 0.100 V, f = 1 MHz, T_A = 25 °C, V_{OUT} = GV_{DD} ÷ 2, V_{OUT} (peak-to-peak) = 0.2 V.

6.2 DDR2 SDRAM AC Electrical Characteristics

This section provides the AC electrical characteristics for the DDR2 SDRAM interface.

6.2.1 DDR2 SDRAM Input AC Timing Specifications

This table provides the input AC timing specifications for the DDR2 SDRAM (GV_{DD}(typ) = 1.8 V).

Table 14. DDR2 SDRAM Input AC Timing Specifications for 1.8-V Interface

At recommended operating conditions with GV_{DD} of 1.8 V± 100mV.

Parameter	Symbol	Min	Max	Unit	Note
AC input low voltage	V_{IL}	—	MVREF – 0.25	V	—
AC input high voltage	V_{IH}	MVREF + 0.25	—	V	—

The following table provides the input AC timing specifications for the DDR2 SDRAM interface.

Table 15. DDR2 SDRAM Input AC Timing Specifications

At recommended operating conditions with GV_{DD} of 1.8V ± 100mV.

Parameter	Symbol	Min	Max	Unit	Note
Controller skew for MDQS—MDQ/MDM	t_{CISKEW}			ps	1, 2

7 Local Bus

This section describes the DC and AC electrical specifications for the local bus interface of the MPC8306S.

7.1 Local Bus DC Electrical Characteristics

The following table provides the DC electrical characteristics for the local bus interface.

Table 17. Local Bus DC Electrical Characteristics

Parameter	Symbol	Min	Max	Unit
High-level input voltage	V_{IH}	2	OV_{DD} + 0.3	V
Low-level input voltage	V_{IL}	–0.3	0.8	V
High-level output voltage, I_{OH} = –100 μA	V_{OH}	OV_{DD} – 0.2	—	V
Low-level output voltage, I_{OL} = 100 μA	V_{OL}	—	0.2	V
Input current	I_{IN}	—	±5	μA

7.2 Local Bus AC Electrical Specifications

The following table describes the general timing parameters of the local bus interface of the MPC8306S.

Table 18. Local Bus General Timing Parameters

Parameter	Symbol[1]	Min	Max	Unit	Note
Local bus cycle time	t_{LBK}	15	—	ns	2
Input setup to local bus clock (LCLK*n*)	t_{LBIVKH}	7	—	ns	3, 4
Input hold from local bus clock (LCLK*n*)	t_{LBIXKH}	1.0	—	ns	3, 4
Local bus clock (LCLK*n*) to output valid	t_{LBKHOV}	—	3	ns	3
Local bus clock (LCLK*n*) to output high impedance for LAD/LDP	t_{LBKHOZ}	—	4	ns	5

Notes:

1. The symbols used for timing specifications follow the pattern of $t_{\text{(first two letters of functional block)(signal)(state)(reference)(state)}}$ for inputs and $t_{\text{(first two letters of functional block)(reference)(state)(signal)(state)}}$ for outputs. For example, $t_{LBIXKH1}$ symbolizes local bus timing (LB) for the input (I) to go invalid (X) with respect to the time the t_{LBK} clock reference (K) goes high (H), in this case for clock one(1).
2. All timings are in reference to falling edge of LCLK0 (for all outputs and for $\overline{\text{LGTA}}$ and LUPWAIT inputs) or rising edge of LCLK0 (for all other inputs).
3. All signals are measured from $OV_{DD}/2$ of the rising/falling edge of LCLK0 to $0.4 \times OV_{DD}$ of the signal in question for 3.3-V signaling levels.
4. Input timings are measured at the pin.
5. For purposes of active/float timing measurements, the Hi-Z or off state is defined to be when the total current delivered through the component pin is less than or equal to the leakage current specification.

Table 19. MII and RMII DC Electrical Characteristics

Parameter	Symbol	Conditions		Min	Max	Unit
Supply voltage 3.3 V	OV_{DD}	—		3	3.6	V
Output high voltage	V_{OH}	I_{OH} = –4.0 mA	OV_{DD} = Min	2.40	OV_{DD} + 0.3	V
Output low voltage	V_{OL}	I_{OL} = 4.0 mA	OV_{DD} = Min	GND	0.50	V
Input high voltage	V_{IH}	—	—	2.0	OV_{DD} + 0.3	V
Input low voltage	V_{IL}	—	—	–0.3	0.90	V
Input current	I_{IN}	$0 V \le V_{IN} \le OV_{DD}$		—	±5	μA

8.2 MII and RMII AC Timing Specifications

The AC timing specifications for MII and RMII are presented in this section.

8.2.1 MII AC Timing Specifications

This section describes the MII transmit and receive AC timing specifications.

8.2.1.1 MII Transmit AC Timing Specifications

The following table provides the MII transmit AC timing specifications.

Table 20. MII Transmit AC Timing Specifications

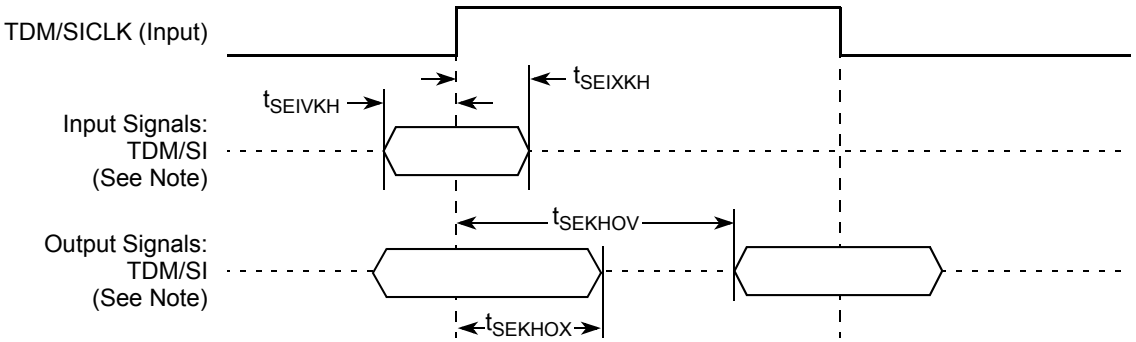
At recommended operating conditions with OV_{DD} of 3.3 V ± 300mV.

Parameter/Condition	Symbol[1]	Min	Typical	Max	Unit
TX_CLK clock period 10 Mbps	t_{MTX}	—	400	—	ns
TX_CLK clock period 100 Mbps	t_{MTX}	—	40	—	ns
TX_CLK duty cycle	t_{MTXH}/t_{MTX}	35	—	65	%
TX_CLK to MII data TXD[3:0], TX_ER, TX_EN delay	t_{MTKHDX}	1	5	15	ns
TX_CLK data clock rise V_{IL}(min) to V_{IH}(max)	t_{MTXR}	1.0	—	4.0	ns
TX_CLK data clock fall V_{IH}(max) to V_{IL}(min)	t_{MTXF}	1.0	—	4.0	ns

Note:

1. The symbols used for timing specifications follow the pattern of $t_{\text{(first two letters of functional block)(signal)(state)(reference)(state)}}$ for inputs and $t_{\text{(first two letters of functional block)(reference)(state)(signal)(state)}}$ for outputs. For example, t_{MTKHDX} symbolizes MII transmit timing (MT) for the time t_{MTX} clock reference (K) going high (H) until data outputs (D) are invalid (X). Note that, in general, the clock reference symbol representation is based on two to three letters representing the clock of a particular functional. For example, the subscript of t_{MTX} represents the MII(M) transmit (TX) clock. For rise and fall times, the latter convention is used with the appropriate letter: R (rise) or F (fall).

The following figure represents the AC timing from Table 27. Note that although the specifications generally reference the rising edge of the clock, these AC timing diagrams also apply when the falling edge is the active edge.



Note: The clock edge is selectable on TDM/SI.

Figure 19. TDM/SI AC Timing (External Clock) Diagram

10 HDLC

This section describes the DC and AC electrical specifications for the high level data link control (HDLC), of the MPC8306S.

10.1 HDLC DC Electrical Characteristics

The following table provides the DC electrical characteristics for the MPC8306S HDLC protocol.

Table 28. HDLC DC Electrical Characteristics

Characteristic	Symbol	Condition	Min	Max	Unit
Output high voltage	V_{OH}	I_{OH} = –2.0 mA	2.4	—	V
Output low voltage	V_{OL}	I_{OL} = 3.2 mA	—	0.5	V
Input high voltage	V_{IH}	—	2.0	OV_{DD} + 0.3	V
Input low voltage	V_{IL}	—	–0.3	0.8	V
Input current	I_{IN}	$0 V \le V_{IN} \le OV_{DD}$	—	±5	μA

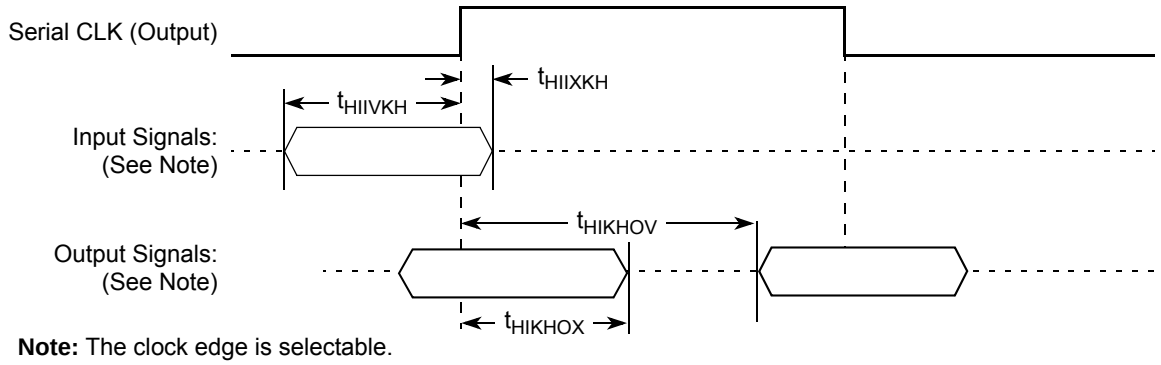
10.2 HDLC AC Timing Specifications

The following table provides the input and output AC timing specifications for HDLC protocol.

Table 29. HDLC AC Timing Specifications[1]

Characteristic	Symbol[2]	Min	Max	Unit
Outputs—Internal clock delay	t_{HIKHOV}	0	9	ns
Outputs—External clock delay	t_{HEKHOV}	1	12	ns
Outputs—Internal clock high impedance	t_{HIKHOX}	0	5.5	ns

The following figure shows the timing with internal clock.



Note: The clock edge is selectable.

Figure 22. AC Timing (Internal Clock) Diagram

11 USB

11.1 USB Controller

This section provides the AC and DC electrical specifications for the USB (ULPI) interface.

11.1.1 USB DC Electrical Characteristics

The following table provides the DC electrical characteristics for the USB interface.

Table 30. USB DC Electrical Characteristics

Parameter	Symbol	Min	Max	Unit
High-level input voltage	V_{IH}	2.0	OV_{DD} + 0.3	V
Low-level input voltage	V_{IL}	–0.3	0.8	V
Input current	I_{IN}	—	±5	μA
High-level output voltage, I_{OH} = –100 μA	V_{OH}	OV_{DD} – 0.2	—	V
Low-level output voltage, I_{OL} = 100 μA	V_{OL}	—	0.2	V

11.1.2 USB AC Electrical Specifications

The following table describes the general timing parameters of the USB interface.

Table 31. USB General Timing Parameters

Parameter	Symbol[1]	Min	Max	Unit	Note
USB clock cycle time	t_{USCK}	15	—	ns	—
Input setup to USB clock—all inputs	t_{USIVKH}	4	—	ns	—
input hold to USB clock—all inputs	t_{USIXKH}	1	—	ns	—
USB clock to output valid—all outputs (except USBDR_STP_USBDR_STP)	t_{USKHOV}	—	7	ns	—

Table 31. USB General Timing Parameters (continued)

Parameter	Symbol[1]	Min	Max	Unit	Note
USB clock to output valid—USBDR_STP	t_{USKHOV}	—	7.5	ns	—
Output hold from USB clock—all outputs	t_{USKHOX}	2	—	ns	—

Note:
1. The symbols used for timing specifications follow the pattern of $t_{\text{(first two letters of functional block)(signal)(state)(reference)(state)}}$ for inputs and $t_{\text{(first two letters of functional block)(reference)(state)(signal)(state)}}$ for outputs. For example, t_{USIXKH} symbolizes USB timing (USB) for the input (I) to go invalid (X) with respect to the time the USB clock reference (K) goes high (H). Also, t_{USKHOX} symbolizes us timing (USB) for the USB clock reference (K) to go high (H), with respect to the output (O) going invalid (X) or output hold time.

The following figures provide the AC test load and signals for the USB, respectively.

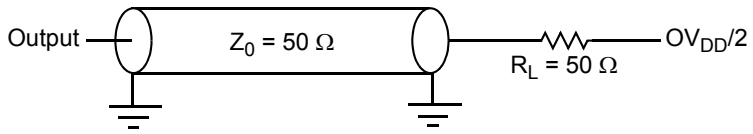


Figure 23. USB AC Test Load

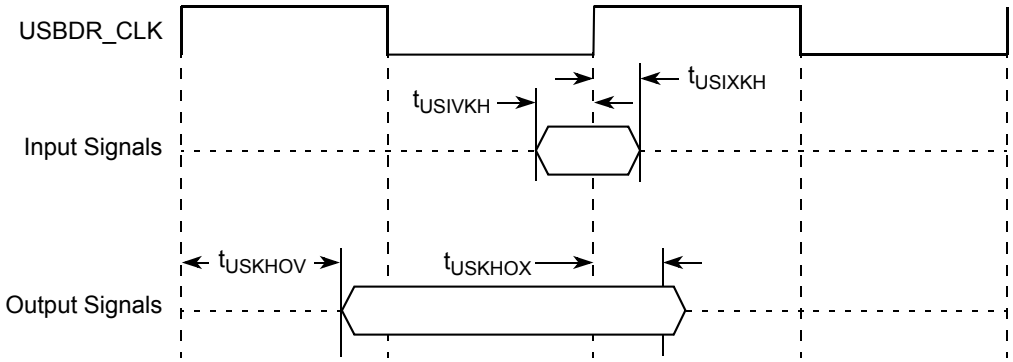


Figure 24. USB Signals

Table 35. I²C AC Electrical Specifications (continued)

All values refer to V_{IH} (min) and V_{IL} (max) levels (see Table 34).

Parameter	Symbol[1]	Min	Max	Unit
Fall time of both SDA and SCL signals	t_{I2CF}	20 + 0.1 C_B[4]	300	ns
Setup time for STOP condition	t_{I2PVKH}	0.6	—	μs
Bus free time between a STOP and START condition	t_{I2KHDX}	1.3	—	μs
Noise margin at the LOW level for each connected device (including hysteresis)	V_{NL}	0.1 × OV_{DD}	—	V
Noise margin at the HIGH level for each connected device (including hysteresis)	V_{NH}	0.2 × OV_{DD}	—	V

Notes:

1. The symbols used for timing specifications follow the pattern of $t_{\text{(first two letters of functional block)(signal)(state)(reference)(state)}}$ for inputs and $t_{\text{(first two letters of functional block)(reference)(state)(signal)(state)}}$ for outputs. For example, t_{I2DVKH} symbolizes I²C timing (I2) with respect to the time data input signals (D) reach the valid state (V) relative to the t_{I2C} clock reference (K) going to the high (H) state or setup time. Also, t_{I2SXKL} symbolizes I²C timing (I2) for the time that the data with respect to the start condition (S) went invalid (X) relative to the t_{I2C} clock reference (K) going to the low (L) state or hold time. Also, t_{I2PVKH} symbolizes I²C timing (I2) for the time that the data with respect to the stop condition (P) reaching the valid state (V) relative to the t_{I2C} clock reference (K) going to the high (H) state or setup time. For rise and fall times, the latter convention is used with the appropriate letter: R (rise) or F (fall).
2. MPC8306S provides a hold time of at least 300 ns for the SDA signal (referred to the V_{IH}(min) of the SCL signal) to bridge the undefined region of the falling edge of SCL.
3. The maximum t_{I2DVKL} has only to be met if the device does not stretch the LOW period (t_{I2CL}) of the SCL signal.
4. C_B = capacitance of one bus line in pF.

The following figure provides the AC test load for the I²C.

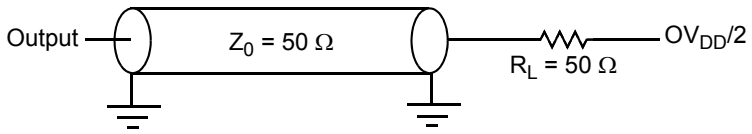


Figure 25. I²C AC Test Load

The following figure shows the AC timing diagram for the I²C bus.

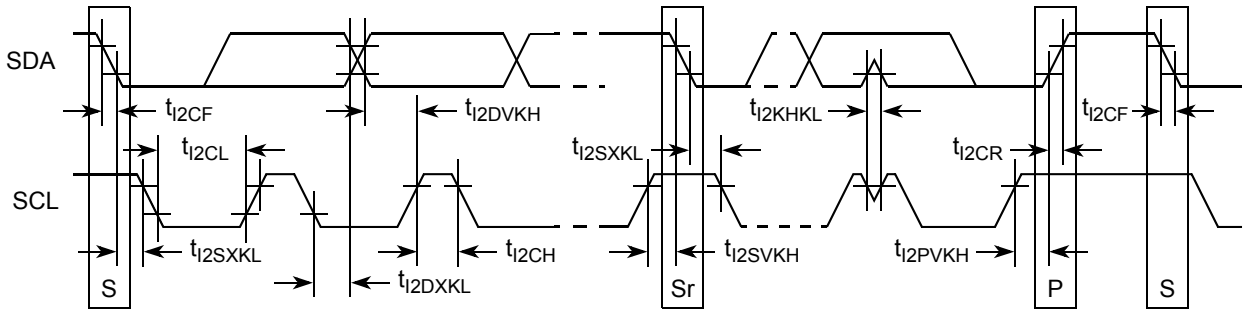


Figure 26. I²C Bus AC Timing Diagram

16 IPIC

This section describes the DC and AC electrical specifications for the external interrupt pins of the MPC8306S.

16.1 IPIC DC Electrical Characteristics

The following table provides the DC electrical characteristics for the external interrupt pins of the MPC8306S.

Table 40. IPIC DC Electrical Characteristics[1,2]

Characteristic	Symbol	Condition	Min	Max	Unit
Input high voltage	V_{IH}	—	2.0	OV_{DD} + 0.3	V
Input low voltage	V_{IL}	—	–0.3	0.8	V
Input current	I_{IN}	—	—	±5	μA
Output High Voltage	V_{OH}	I_{OL} = -8.0 mA	2.4	—	V
Output low voltage	V_{OL}	I_{OL} = 6.0 mA	—	0.5	V
Output low voltage	V_{OL}	I_{OL} = 3.2 mA	—	0.4	V

Notes:
1. This table applies for pins $\overline{\text{IRQ}}$, $\overline{\text{MCP\_OUT}}$, and QE ports Interrupts.
2. $\overline{\text{MCP\_OUT}}$ is open drain pins, thus V_{OH} is not relevant for those pins.

16.2 IPIC AC Timing Specifications

The following table provides the IPIC input and output AC timing specifications.

Table 41. IPIC Input AC Timing Specifications[1]

Characteristic	Symbol[2]	Min	Unit
IPIC inputs—minimum pulse width	t_{PIWID}	20	ns

Notes:
1. Input specifications are measured from the 50% level of the signal to the 50% level of the rising edge of SYS_CLK_IN. Timings are measured at the pin.
2. IPIC inputs and outputs are asynchronous to any visible clock. IPIC outputs should be synchronized before use by any external synchronous logic. IPIC inputs are required to be valid for at least t_{PIWID} ns to ensure proper operation when working in edge triggered mode.

17 SPI

This section describes the DC and AC electrical specifications for the SPI of the MPC8306S.

17.1 SPI DC Electrical Characteristics

The following table provides the DC electrical characteristics for the MPC8306S SPI.

Table 42. SPI DC Electrical Characteristics

Characteristic	Symbol	Condition	Min	Max	Unit
Output high voltage	V_{OH}	I_{OH} = –6.0 mA	2.4	—	V
Output low voltage	V_{OL}	I_{OL} = 6.0 mA	—	0.5	V
Output low voltage	V_{OL}	I_{OL} = 3.2 mA	—	0.4	V
Input high voltage	V_{IH}	—	2.0	OV_{DD} + 0.3	V
Input low voltage	V_{IL}	—	–0.3	0.8	V
Input current	I_{IN}	$0 V \le V_{IN} \le OV_{DD}$	—	±5	μA

17.2 SPI AC Timing Specifications

The following table and provide the SPI input and output AC timing specifications.

Table 43. SPI AC Timing Specifications[1]

Characteristic	Symbol[2]	Min	Max	Unit
SPI outputs—Master mode (internal clock) delay	t_{NIKHOV}	0.5	6	ns
SPI outputs—Slave mode (external clock) delay	t_{NEKHOV}	2	8	ns
SPI inputs—Master mode (internal clock) input setup time	t_{NIIVKH}	6	—	ns
SPI inputs—Master mode (internal clock) input hold time	t_{NIIXKH}	0	—	ns
SPI inputs—Slave mode (external clock) input setup time	t_{NEIVKH}	4	—	ns
SPI inputs—Slave mode (external clock) input hold time	t_{NEIXKH}	2	—	ns

Notes:
1. Output specifications are measured from the 50% level of the rising edge of SPICLK to the 50% level of the signal. Timings are measured at the pin.
2. The symbols used for timing specifications follow the pattern of $t_{\text{(first two letters of functional block)(signal)(state)(reference)(state)}}$ for inputs and $t_{\text{(first two letters of functional block)(reference)(state)(signal)(state)}}$ for outputs. For example, t_{NIKHOV} symbolizes the NMSI outputs internal timing (NI) for the time t_{SPI} memory clock reference (K) goes from the high state (H) until outputs (O) are valid (V).
3. All units of output delay must be enabled for 8306S output port spimosi (SPI Master Mode)
4. delay units must not be enabled for Slave Mode.

The following figure provides the AC test load for the SPI.

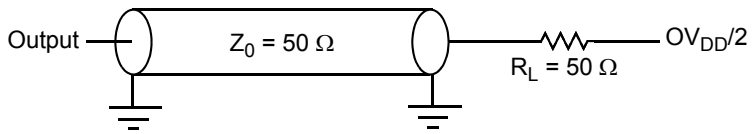


Figure 29. SPI AC Test Load

Figure 30 and Figure 31 represent the AC timing from Table 43. Note that although the specifications generally reference the rising edge of the clock, these AC timing diagrams also apply when the falling edge is the active edge.

The following figure provides the boundary-scan timing diagram.

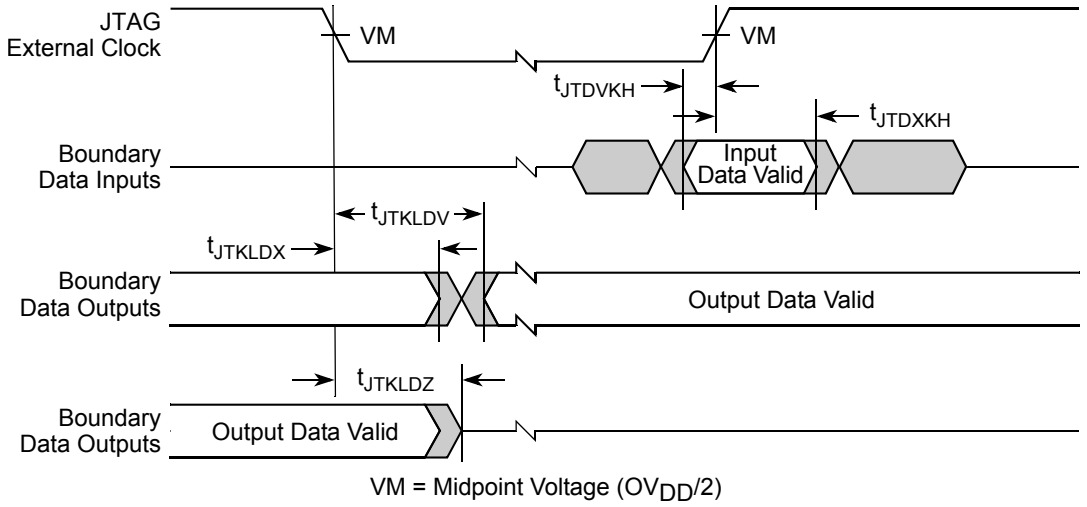


Figure 35. Boundary-Scan Timing Diagram

The following figure provides the test access port timing diagram.

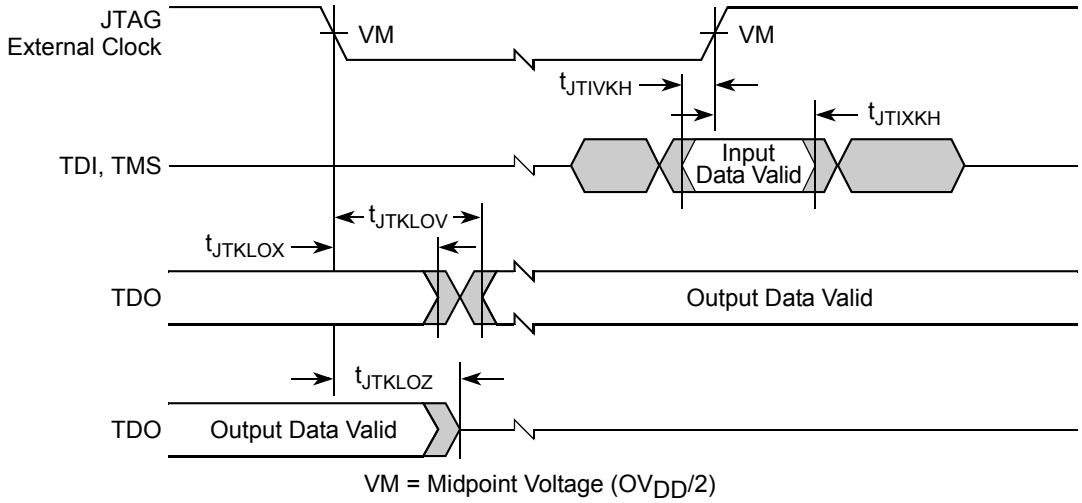


Figure 36. Test Access Port Timing Diagram

Table 46. MPC8306S Pinout Listing (continued)

Signal	Package Pin Number	Pin Type	Power Supply	Notes
MEMC_MA[8]	T1	O	GV_{DD}	—
MEMC_MA[9]	P4	O	GV_{DD}	—
MEMC_MA[10]	L4	O	GV_{DD}	—
MEMC_MA[11]	T2	O	GV_{DD}	—
MEMC_MA[12]	U1	O	GV_{DD}	—
MEMC_MA[13]	U2	O	GV_{DD}	—
MEMC_MWE_B	K1	O	GV_{DD}	—
MEMC_MRAS_B	K2	O	GV_{DD}	—
MEMC_MCAS_B	J1	O	GV_{DD}	—
MEMC_MCS_B[0]	J4	O	GV_{DD}	—
MEMC_MCS_B[1]	H1	O	GV_{DD}	—
MEMC_MCKE[0]	U4	O	GV_{DD}	—
MEMC_MCK[0]	V1	O	GV_{DD}	—
MEMC_MCK_B[0]	W1	O	GV_{DD}	—
MEMC_MODT[0]	H2	O	GV_{DD}	—
MEMC_MODT[1]	H4	O	GV_{DD}	—
MEMC_MVREF	L8		GV_{DD}	—
Local Bus Controller Interface				
LAD[0]	B7	IO	OV_{DD}	—
LAD[1]	D9	IO	OV_{DD}	—
LAD[2]	A6	IO	OV_{DD}	—
LAD[3]	B8	IO	OV_{DD}	—
LAD[4]	A7	IO	OV_{DD}	—
LAD[5]	A8	IO	OV_{DD}	—
LAD[6]	A9	IO	OV_{DD}	—
LAD[7]	D10	IO	OV_{DD}	—
LAD[8]	B10	IO	OV_{DD}	—
LAD[9]	A10	IO	OV_{DD}	—
LAD[10]	B11	IO	OV_{DD}	—
LAD[11]	D12	IO	OV_{DD}	—
LAD[12]	D11	IO	OV_{DD}	—
LAD[13]	A11	IO	OV_{DD}	—
LAD[14]	A12	IO	OV_{DD}	—
LAD[15]	B13	IO	OV_{DD}	—
LA[16]	A13	IO	OV_{DD}	—

Table 46. MPC8306S Pinout Listing (continued)

Signal	Package Pin Number	Pin Type	Power Supply	Notes
USBDR_TXDRXD[7]/GPIO[37]/QE_BRG[11]	Y5	IO	OV_{DD}	—
DUART				
UART1_SOUT[1]/LSRCID4/LCS_B[4]	C23	O	OV_{DD}	—
UART1_SIN[1]/LDVAL/LCS_B[5]	F19	IO	OV_{DD}	—
UART1_SOUT[2]/UART1_RTS_B1/LCS_B[6]	D23	O	OV_{DD}	—
UART1_SIN[2]/UART1_CTS_B[1]/LCS_B[7]	D22	IO	OV_{DD}	—
Interrupts				
IRQ_B0_MCP_IN_B/CE_PI_0	E20	IO	OV_{DD}	—
IRQ_B1/MCP_OUT_B	E23	IO	OV_{DD}	—
IRQ_B2/CKSTOP_OUT_B	E22	IO	OV_{DD}	—
IRQ_B3/CKSTOP_IN_B	F20	I	OV_{DD}	—
I2C / SPI				
IIC_SDA1	G20	IO	OV_{DD}	2
IIC_SCL1	J20	IO	OV_{DD}	2
LCLK1/IIC_SCL2/CKSTOP_IN_B	H20	IO	OV_{DD}	2
SPISEL_BOOT/IIC_SDA2/CKSTOP_OUT_B	F23	O	OV_{DD}	2
SPIMOSI/LSRCID[2]	G22	IO	OV_{DD}	—
SPIMISO/LSRCID[3]	K20	IO	OV_{DD}	—
SPICLK/LSRCID[0]	G23	IO	OV_{DD}	—
SPISEL/LSRCID[1]	H22	I	OV_{DD}	—
FEC Management				
FEC_MDC	H23	O	OV_{DD}	—
FEC_MDIO	L20	IO	OV_{DD}	—
FEC1/GTM/GPIO				
FEC1_COL/GTM1_TIN[1]/GPIO[16]	AB20	IO	OV_{DD}	—
FEC1_CRS/GTM1_TGATE1_B/GPIO[17]	AC21	IO	OV_{DD}	—
FEC1_RX_CLK/GPIO[18]	Y17	IO	OV_{DD}	—
FEC1_RX_DV/GTM1_TIN[2]/GPIO[19]	Y18	IO	OV_{DD}	—
FEC1_RX_ER/GTM1_TGATE[2]_B/GPIO[20]	AB19	IO	OV_{DD}	—
FEC1_RXD0/GPIO[21]	AC20	IO	OV_{DD}	—
FEC1_RXD1/GTM1_TIN[3]/GPIO[22]	AC19	IO	OV_{DD}	—
FEC1_RXD2/GTM1_TGATE[3]_B/GPIO[23]	AC18	IO	OV_{DD}	—
FEC1_RXD3/GPIO[24]	AB17	IO	OV_{DD}	—
FEC1_TX_CLK/GTM1_TIN4/GPIO[25]	Y15	IO	OV_{DD}	—
FEC1_TX_EN/GTM1_TGATE[4]_B/GPIO[26]	Y16	IO	OV_{DD}	—

20 Clocking

The following figure Figure 39 shows the internal distribution of clocks within the MPC8306S.

Figure 38. MPC8306S Clock Subsystem

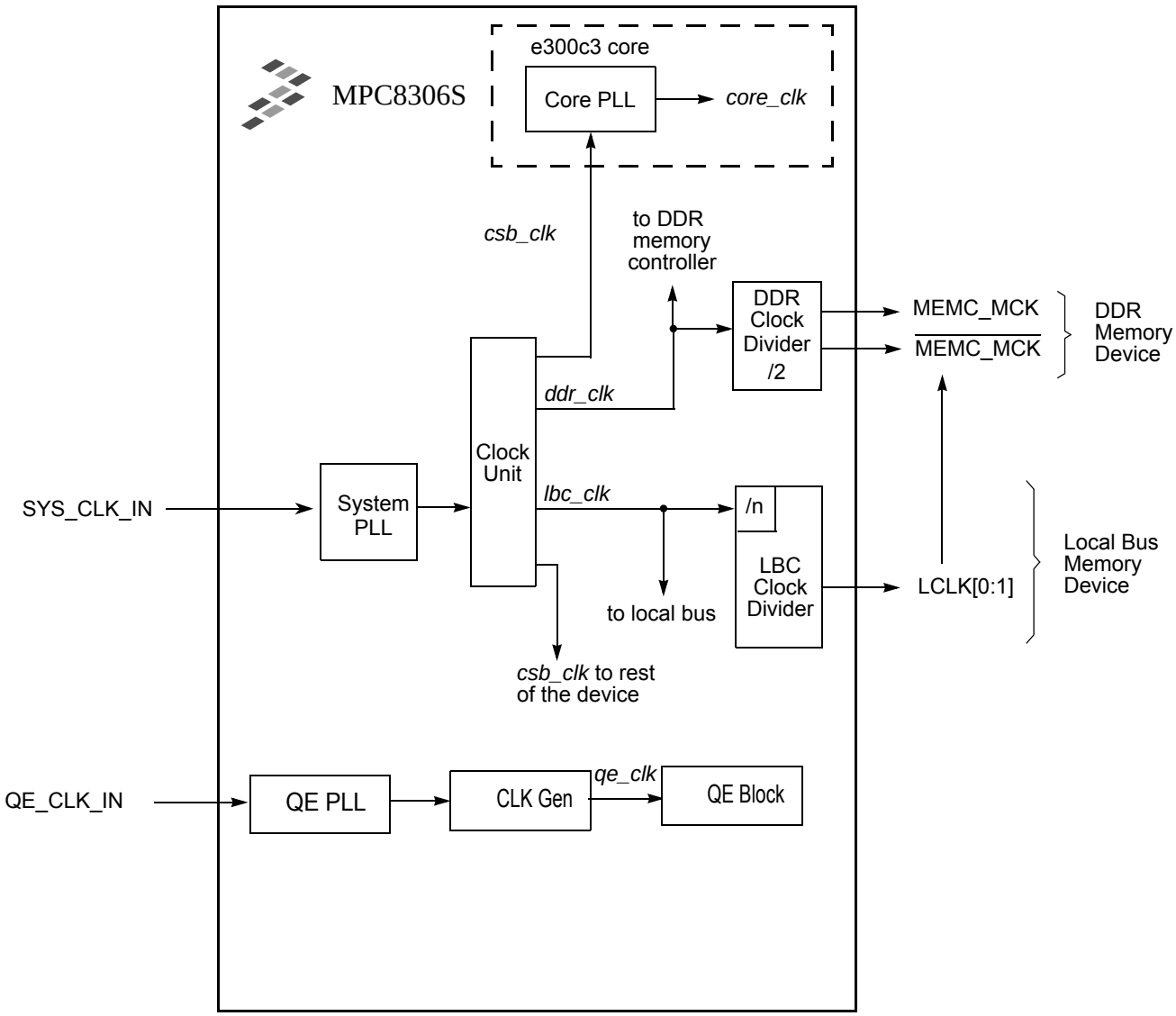


Figure 39. MPC8306S Clock Subsystem

The primary clock source for MPC8306S is SYS_CLK_IN.

Figure 40.

In addition, some of the internal units may be required to be shut off or operate at lower frequency than the *csb_clk* frequency. These units have a default clock ratio that can be configured by a memory mapped register after the device comes out of reset.

The following table specifies which units have a configurable clock frequency. For detailed description, refer to the "System Clock Control Register (SCCR)" section in the *MPC8306S PowerQUICC II Pro Integrated Communications Processor Family Reference Manual*.

Table 47. Configurable Clock Units

Unit	Default Frequency	Options
I2C,SDHC, USB, DMA Complex	*csb_clk*	Off, csb_clk, *csb_clk*/2, *csb_clk*/3

NOTE

Setting the clock ratio of these units must be performed prior to any access to them.

The following table provides the maximum operating frequencies for the MPC8306S MAPBGA under recommended operating conditions (see Table 2).

Table 48. Operating Frequencies for MAPBGA

Characteristic[1]	Max Operating Frequency	Unit
e300 core frequency (*core_clk*)	266	MHz
Coherent system bus frequency (*csb_clk*)	133	MHz
QUICC Engine frequency (*qe_clk*)	233	MHz
DDR2 memory bus frequency (MCLK)[2]	167	MHz
Local bus frequency (LCLK*n*)[3]	66	MHz

Notes:
1. The SYS_CLK_IN frequency, RCWL[SPMF], and RCWL[COREPLL] settings must be chosen such that the resulting csb_clk, MCLK, LCLK, and core_clk frequencies do not exceed their respective maximum or minimum operating frequencies.
2. The DDR2 data rate is 2× the DDR2 memory bus frequency.
3. The local bus frequency is 1/2, 1/4, or 1/8 of the lb_clk frequency (depending on LCRR[CLKDIV]) which is in turn 1× or 2× the csb_clk frequency (depending on RCWL[LBCM]).

20.2 System PLL Configuration

The system PLL is controlled by the RCWL[SPMF] parameter. Table 49 shows the multiplication factor encodings for the system PLL.

NOTE

System PLL VCO frequency = 2 × (CSB frequency) × (System PLL VCO divider). The VCO divider needs to be set properly so that the System PLL VCO frequency is in the range of 450–750 MHz.

As described in Section 20, "Clocking," the LBCM, DDRCM, and SPMF parameters in the reset configuration word low select the ratio between the primary clock input (*SYS_CLK_IN)* and the internal

Table 49. System PLL Multiplication Factors

RCWL[SPMF]	System PLL Multiplication Factor
0000	Reserved
0001	Reserved
0010	× 2
0011	× 3
0100	× 4
0101	× 5
0110	× 6
0111–1111	Reserved

coherent system bus clock (*csb_clk*). The following table shows the expected frequency values for the CSB frequency for selected *csb_clk* to *SYS_CLK_IN* ratios.

Table 50. CSB Frequency Options

SPMF	csb_clk : sys_clk_in Ratio	SYS_CLK_IN(MHz)		
		25	33.33	66.67
		csb_clk Frequency (MHz)		
0010	2:1			133
0011	3:1			
0100	4:1		133	
0101	5:1	125	167	
0110	6:1			

20.3 Core PLL Configuration

RCWL[COREPLL] selects the ratio between the internal coherent system bus clock (*csb_clk*) and the e300 core clock (*core_clk*). The following table shows the encodings for RCWL[COREPLL]. COREPLL values not listed, and should be considered reserved.

Table 51. e300 Core PLL Configuration

RCWL[COREPLL]			*core_clk* : *csb_clk* Ratio	VCO Divider
0-1	2-5	6		
nn	0000	n	PLL bypassed (PLL off, *csb_clk* clocks core directly)	PLL bypassed (PLL off, *csb_clk* clocks core directly)
00	0001	0	1:1	÷2
01	0001	0	1:1	÷4
10	0001	0	1:1	÷8
11	0001	0	1:1	÷8

21 Thermal

This section describes the thermal specifications of the MPC8306S.

21.1 Thermal Characteristics

The following table provides the package thermal characteristics for the 369, 19 × 19 mm MAPBGA of the MPC8306S.

Table 55. Package Thermal Characteristics for MAPBGA

Characteristic	Board type	Symbol	Value	Unit	Notes
Junction-to-ambient natural convection	Single-layer board (1s)	$R_{\theta JA}$	39	°C/W	1, 2
Junction-to-ambient natural convection	Four-layer board (2s2p)	$R_{\theta JA}$	24	°C/W	1, 2, 3
Junction-to-ambient (@200 ft/min)	Single-layer board (1s)	$R_{\theta JMA}$	32	°C/W	1, 3
Junction-to-ambient (@200 ft/min)	Four-layer board (2s2p)	$R_{\theta JMA}$	21	°C/W	1, 3
Junction-to-board	—	$R_{\theta JB}$	14	°C/W	4
Junction-to-case	—	$R_{\theta JC}$	9	°C/W	5
Junction-to-package top	Natural convection	Ψ_{JT}	2	°C/W	6

Notes:
1. Junction temperature is a function of die size, on-chip power dissipation, package thermal resistance, mounting site (board) temperature, ambient temperature, air flow, power dissipation of other components on the board, and board thermal resistance.
2. Per JEDEC JESD51-2 with the single layer board horizontal. Board meets JESD51-9 specification.
3. Per JEDEC JESD51-6 with the board horizontal.
4. Thermal resistance between the die and the printed-circuit board per JEDEC JESD51-8. Board temperature is measured on the top surface of the board near the package.
5. Thermal resistance between the die and the case top surface as measured by the cold plate method (MIL SPEC-883 Method 1012.1).
6. Thermal characterization parameter indicating the temperature difference between package top and the junction temperature per JEDEC JESD51-2. When Greek letters are not available, the thermal characterization parameter is written as Psi-JT.

21.1.1 Thermal Management Information

For the following sections, $P_D = (V_{DD} \times I_{DD}) + P_{I/O}$, where $P_{I/O}$ is the power dissipation of the I/O drivers.

21.1.2 Estimation of Junction Temperature with Junction-to-Ambient Thermal Resistance

An estimation of the chip junction temperature, T_J, can be obtained from the equation:

$$T_J = T_A + (R_{\theta JA} \times P_D) \qquad \textit{Eqn. 1}$$

where:

T_J = junction temperature (°C)